

Supporting information

The hydrothermal synthesis, crystal structure and electrochemical properties of MnSb₂O₄

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1. High resolution PXRD

Low temperature patterns were collected at 105, 150, 200, 250, 300 and 350 K. High temperature was collected at HT1: 300, 380, 420, 460, 520, 560, 620, 660 K and HT2: 300, 380, 420, 560, 660, 760 and 850 K. The wavelength was calibrated with a NIST CeO₂ standard. The wavelength was 0.500345(2) Å, 0.500256(2) Å and 0.500176(2) Å during three different beamtimes.

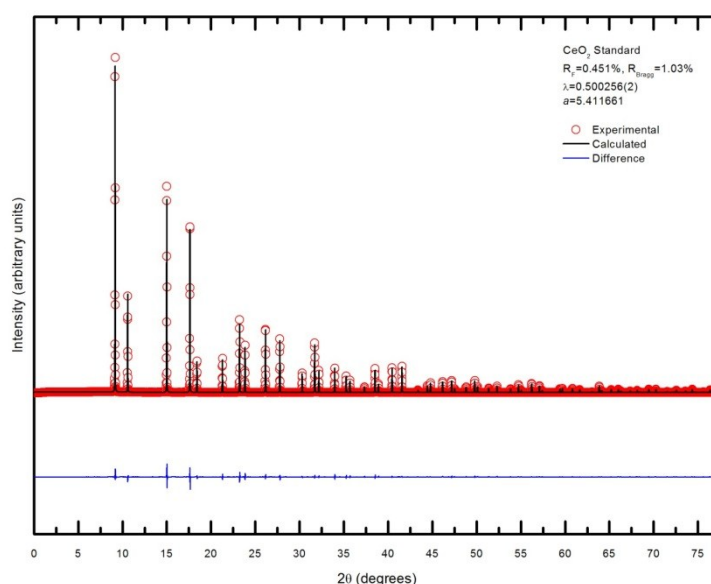


Figure S.1: Wavelength calibrations at the BL44B2 beamline using CeO₂.

In figure S.2 the cell axes for three measurements of two samples of MnSb₂O₄. The left and middle part shows the same trend is reproduced when re-measured. The right part shows a different sample reproducing the same trend, but to a different degree. Reliability factors and atomic displacement parameters from the Rietveld refinements are given in table S.1 and S.2.

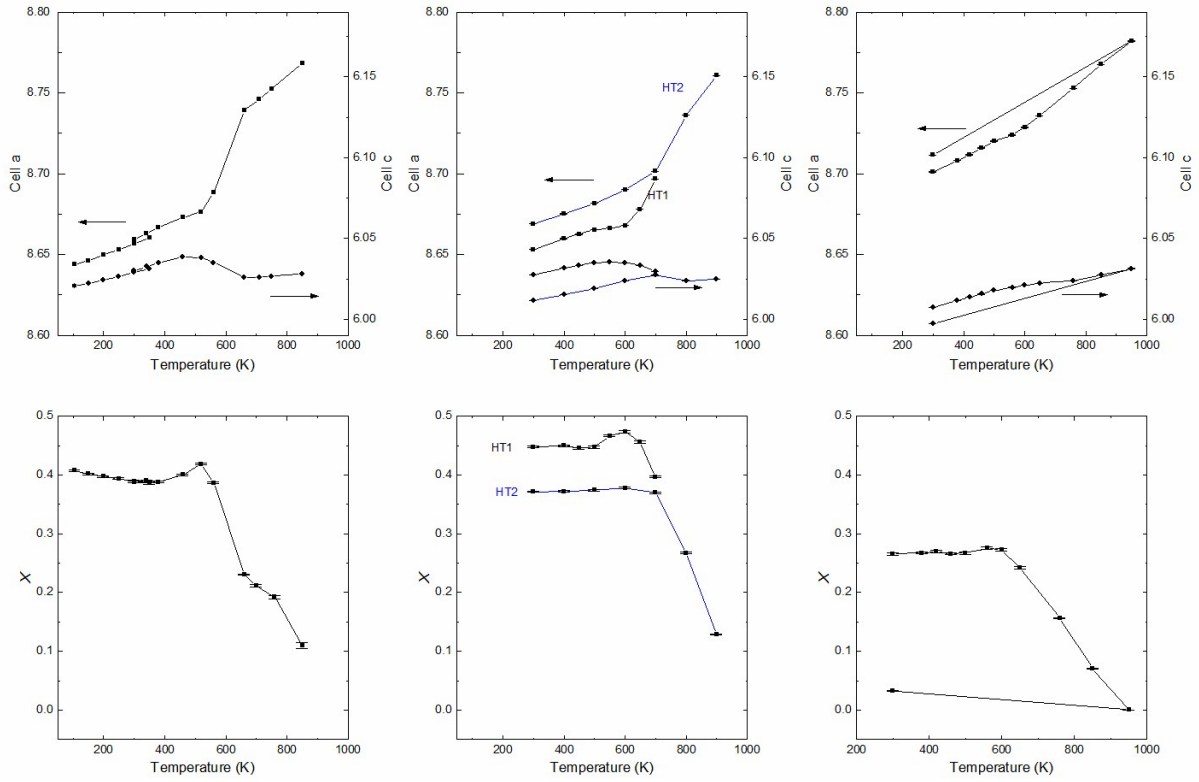


Figure S.2: Cell axes and X peak profile parameter for three samples measured. Left: 105-350 K (glass), 300-850 K (quartz). Middle: 300-660 K (HT1) and 300-850 K (HT2). Right: 300-950 K and 300 K.

Table S.1: Reliability factors from 105 – 850 K

| T (K) | R_p | R_{wp} | R_{exp} | χ^2 | R_B | R_F |
|------------|-------|----------|-----------|----------|-------|-------|
| LT | | | | | | |
| 105 | 10.1 | 10.8 | 4.2 | 6.597 | 3.38 | 2.41 |
| 150 | 10.2 | 10.9 | 4.21 | 6.66 | 3.29 | 2.48 |
| 200 | 10.5 | 11.1 | 4.26 | 6.805 | 3.4 | 2.53 |
| 250 | 10.6 | 11.3 | 4.29 | 6.882 | 3.25 | 2.71 |
| 300 | 10.9 | 11.4 | 4.33 | 6.909 | 3.25 | 3.04 |
| 350 | 10.9 | 11.3 | 4.37 | 6.706 | 3.36 | 3.12 |
| HT1 | | | | | | |
| 300 | 11.4 | 10.4 | 10.1 | 1069 | 4.43 | 3.41 |
| 380 | 11.4 | 10.3 | 10.2 | 1008 | 3.85 | 3.81 |
| 420 | 11.6 | 10.2 | 10.2 | 1000 | 3.86 | 3.7 |
| 460 | 11.6 | 10.3 | 10.4 | 0.9795 | 4.43 | 4.25 |
| 520 | 11.6 | 10.1 | 10.4 | 0.9434 | 5.67 | 4.51 |
| 560 | 12.2 | 10.7 | 10.4 | 1064 | 8.37 | 5.48 |
| 620 | 12.6 | 11.3 | 10.3 | 1213 | 18.2 | 5.6 |
| 660 | 11.2 | 10.1 | 10 | 1003 | 4.72 | 5.86 |
| HT2 | | | | | | |
| 300 | 10.2 | 9.88 | 9.04 | 1194 | 3.61 | 3.18 |
| 380 | 10.3 | 9.81 | 9.14 | 1154 | 3.57 | 3.65 |
| 460 | 10.6 | 9.83 | 9.24 | 1132 | 3.61 | 3.75 |
| 560 | 10.7 | 9.83 | 9.46 | 1081 | 3.77 | 5.02 |
| 660 | 10.6 | 9.45 | 9.59 | 0.971 | 3.7 | 5.8 |
| 760 | 9.23 | 8.36 | 8.16 | 1050 | 2.51 | 6.85 |
| 850 | 11.5 | 10.1 | 8.24 | 1.502 | 2.64 | 12.2 |

Table S.2: Atomic displacement parameters for MnSb₂O₄ (LT, HT1 and HT2).

| Temperature (K) | U _{eq} (Mn) (Å ²) | U _{eq} (Sb) (Å ²) | U _{eq} (O1) (Å ²) | U _{eq} (O2) (Å ²) |
|-----------------|--|--|--|--|
| LT | | | | |
| 105 | 0.003(4) | 0.0118(7) | 0.008(2) | 0.007(2) |
| 150 | 0.0012(4) | 0.0130(7) | 0.009(2) | 0.008(2) |
| 200 | 0.0020(5) | 0.0145(8) | 0.010(2) | 0.007(2) |
| 250 | 0.0032(5) | 0.0160(8) | 0.011(2) | 0.008(2) |
| 300 | 0.0043(5) | 0.0177(8) | 0.014(2) | 0.011(2) |
| 350 | 0.0050(5) | 0.0195(9) | 0.015(2) | 0.012(2) |
| HT1 | | | | |
| 300 | 0.0036(5) | 0.0191(9) | 0.014(2) | 0.014(2) |
| 400 | 0.0050(5) | 0.0216(9) | 0.018(2) | 0.019(2) |
| 450 | 0.0058(5) | 0.0229(9) | 0.014(2) | 0.019(2) |
| 500 | 0.0064(5) | 0.024(1) | 0.018(2) | 0.021(3) |
| 550 | 0.0076(6) | 0.026(1) | 0.018(2) | 0.022(3) |
| 600 | 0.0090(6) | 0.028(1) | 0.020(2) | 0.025(3) |
| 650 | 0.0115(6) | 0.028(1) | 0.019(2) | 0.027(3) |
| 700 | 0.0137(6) | 0.0273(9) | 0.021(2) | 0.030(3) |
| HT2 | | | | |
| 300 | 0.0049(4) | 0.0147(7) | 0.011(2) | 0.009(2) |
| 400 | 0.0067(5) | 0.0173(7) | 0.013(2) | 0.011(2) |
| 500 | 0.0090(5) | 0.0204(8) | 0.016(2) | 0.015(2) |
| 600 | 0.0114(5) | 0.0232(8) | 0.019(2) | 0.018(2) |
| 700 | 0.0137(5) | 0.0261(8) | 0.024(2) | 0.024(2) |
| 800 | 0.0210(4) | 0.0278(6) | 0.027(1) | 0.029(2) |
| 900 | 0.0263(5) | 0.0315(6) | 0.033(2) | 0.037(2) |

2. Evolution of cell parameters from SCXRD

The cell parameters of a MnSb₂O₄ crystal is plotted against temperature in Figure S.3. The data was acquired in one series from 100-475 K and subsequently from 475-100 K, and normalized to the first temperature at 300 K. Fluctuations in the cell parameters are either due to a systematic error in the setup or changes to the sample (decomposition/gas uptake). All measured diffraction data have been measured using the same experimental setup (SuperNova diffractometer), with the same measuring strategy and the same orientation of the crystal.

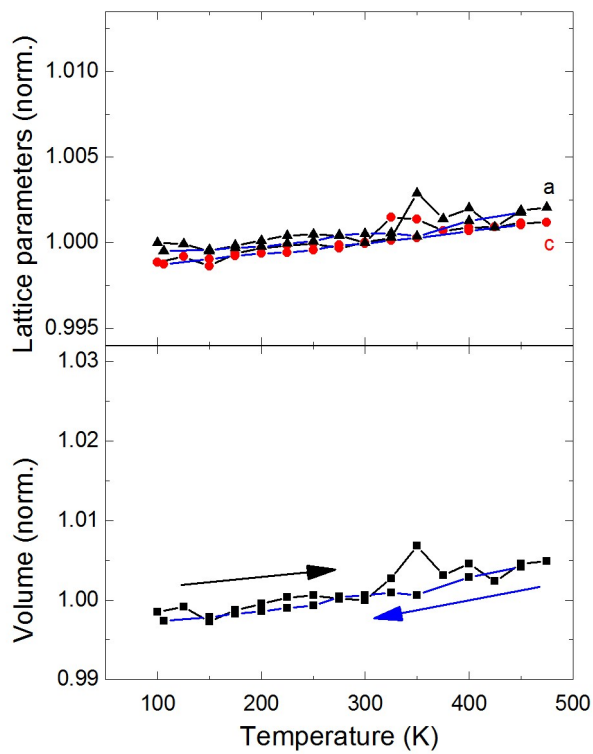


Figure S.3: Normalized cell parameters for MnSb_2O_4 as function of temperature. Diffraction data have been measured from 100 K up to 475 K (black lines) and then also upon cooling the sample down to 100 K (blue lines).

3. Thermogravimetry

Figure S.4 shows PXRD obtained of MnSb_2O_4 that was heated up to 1000 K with oxygen present and three standard PXRD patterns to describe all reflections.

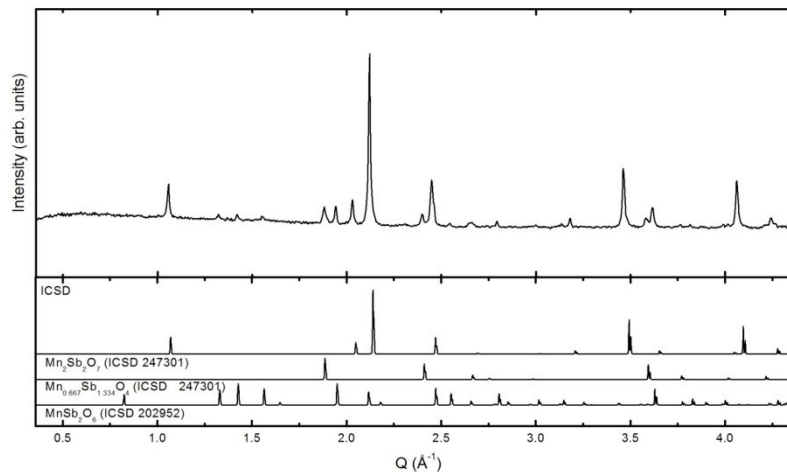


Figure S.4: PXRD of MnSb_2O_4 after being heated to 1000 K with oxygen present and simulated patterns from ICSD. Oxidation has occurred with a mass increase of 8%.

4. FTIR

Figure S.5 shows FTIR of the as-synthesised MnSb_2O_4 particles and particles that were washed with deionised water.

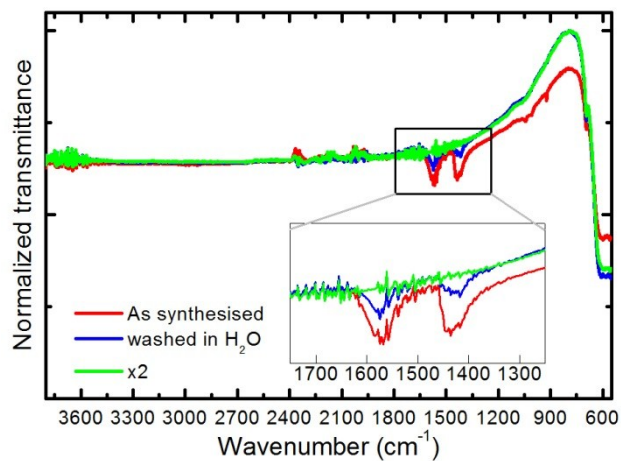


Figure S.5: FTIR of MnSb_2O_4 before/after wash/decant procedure.

5. Na-ion half-cell electrochemical performance

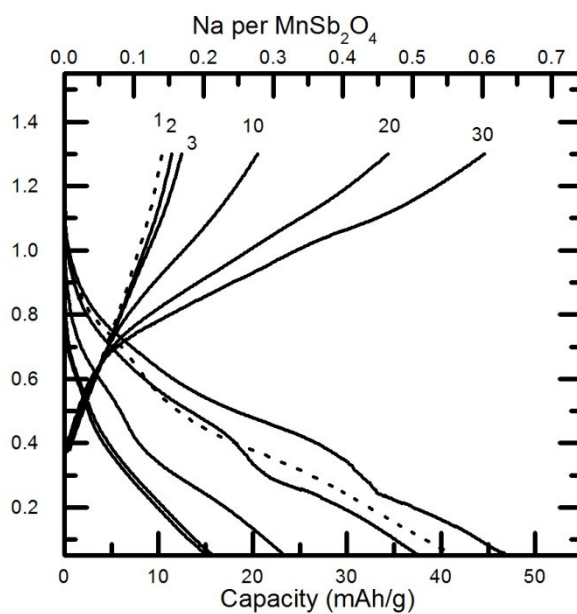


Figure S.6: Potential (vs. Na/Na^+) vs. capacity for MnSb_2O_4 under galvanostatic charge/discharge at 30 mA/g between 0.05-1.3 V.